

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	497	((high near dielectric near (film or layer)) same metal same (oxide or oxygen) same silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:38
L2	55	((high near dielectric near (film or layer)) same metal same (oxide or oxygen) same silicon) same (barrier adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:38
L3	4	((high near dielectric near (film or layer)) same metal near5 (oxide or oxygen) near5 silicon) same (barrier adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:38
L4	4	((high near dielectric near (film or layer)) same (metal near5 (oxide or oxygen) near5 silicon)) same (barrier adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:45
L5	8	((high near dielectric near2 (film or layer)) same (metal near5 (oxide or oxygen) near5 silicon)) same (barrier adj (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:49
L6	2	10/122366	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:47
L7	10902	((high near dielectric) or high-k) near2 (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:49
L8	2514	((high near dielectric) or high-k) near2 (film or layer)) and (barrier near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:49
L9	847	((high near dielectric) or high-k) near2 (film or layer)) same (barrier near (film or layer))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:50

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L10	84	((((high near dielectric) or high-k) near2 (film or layer)) same (barrier near (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:51
L11	7	((((high near dielectric) or high-k) near2 (film or layer)) same (gate adj electrode) same (gate adj (insulating or dielectric or insulator or insulation)) same (barrier near (film or layer))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:51
L12	62	((((high near dielectric) or high-k) near2 (film or layer)) same (gate adj electrode) same (gate adj (insulating or dielectric or insulator or insulation)) same (barrier near (film or layer)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:53
L13	55	((((high near dielectric) or high-k) near2 (film or layer)) same (gate adj electrode) same (gate adj (insulating or dielectric or insulator or insulation)) same (barrier near (film or layer))) and (((high-k) or (high near dielectric)) near10 (oxide or oxygen)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:53
L14	23	((((high near dielectric) or high-k) near2 (film or layer)) same (gate adj electrode) same (gate adj (insulating or dielectric or insulator or insulation)) same (barrier near (film or layer))) and (((high-k) or (high near dielectric)) near10 (oxide or oxygen))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:54
L15	255	(((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 08:55
L16	32	(((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon).clm. and barrier.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:01
L17	149	(((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon).clm. and (gate adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:02

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L18	30	((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon).clm. same (gate adj electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:06
L19	95	((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon) same (gate adj oxide) same (gate adj (insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:06
L20	41	((high-k) or (high near dielectric)) near10 (oxide or oxygen) near10 silicon) same (gate adj oxide) same (gate adj (insulating or dielectric)) same substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:09
L21	139	"6013553"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:10
L22	2	"6013553".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:11
L23	2	"6521911".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:11
L24	2516	((high-k) or (high near dielectric)) with metal near5 (oxide or oxygen)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:12
L25	2516	((high-k) or (high near dielectric)) with (metal near5 (oxide or oxygen)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:12
L26	252	((high-k) or (high near dielectric)) with (metal near5 (oxide or oxygen))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:13
L27	73	((high-k) or (high near dielectric)) near (film or layer) with (metal near5 (oxide or oxygen))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:15

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L28	7	((((high-k) or (high near dielectric)) near (film or layer)) with (metal near5 silicon near5 (oxide or oxygen))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:16
L29	67	((((high-k) or (high near dielectric)) near (film or layer)) with (metal near5 silicon near5 (oxide or oxygen)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:19
L30	42	"6060755"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 09:19